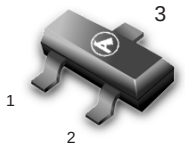
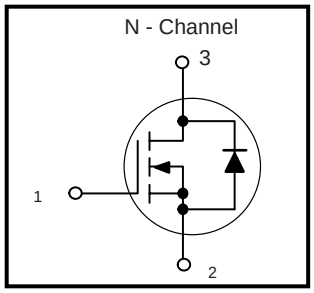
Small Signal MOSFET
115 mAmps, 60 Volts
N–Channel SOT–23

L2N7002LT1



CASE 318, STYLE 21
SOT– 23 (TO–236AB)

115 mAMPS
60 VOLTS
$R_{DS(on)}$ = 7.5 Ω



MAXIMUM RATINGS

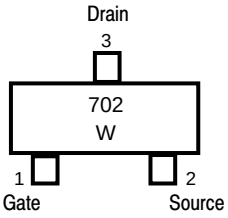
Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DSS}	60	Vdc
Drain–Gate Voltage (R_{GS} = 1.0 MΩ)	V_{DGR}	60	Vdc
Drain Current – Continuous T_C = 25°C (Note 1.) T_C = 100°C (Note 1.) – Pulsed (Note 2.)	I_D I_D I_{DM}	±115 ±75 ±800	mAdc
Gate–Source Voltage – Continuous – Non–repetitive ($t_p \leq 50$ µs)	V_{GS} V_{GSM}	±20 ±40	Vdc Vpk

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 3.) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate,(Note 4.) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.
3. FR–5 = 1.0 x 0.75 x 0.062 in.
4. Alumina = 0.4 x 0.3 x 0.025 in 99.5% alumina.

MARKING DIAGRAM & PIN ASSIGNMENT



702 = Device Code
W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
2N7002LT1	SOT–23	3000 Tape & Reel
2N7002LT3	SOT–23	10,000 Tape & Reel

L2N7002LT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μAdc)		$V_{(BR)DSS}$	60	–	–	Vdc
Zero Gate Voltage Drain Current (V_{GS} = 0, V_{DS} = 60 Vdc)	T_J = 25°C T_J = 125°C	I_{DSS}	– –	– –	1.0 500	μAdc
Gate–Body Leakage Current, Forward (V_{GS} = 20 Vdc)		I_{GSSF}	–	–	100	nAdc
Gate–Body Leakage Current, Reverse (V_{GS} = –20 Vdc)		I_{GSSR}	–	–	–100	nAdc
ON CHARACTERISTICS (Note 2.)						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μAdc)		$V_{GS(th)}$	1.0	–	2.5	Vdc
On–State Drain Current (V_{DS} ≥ 2.0 $V_{DS(on)}$, V_{GS} = 10 Vdc)		$I_{D(on)}$	500	–	–	mA
Static Drain–Source On–State Voltage (V_{GS} = 10 Vdc, I_D = 500 mAdc) (V_{GS} = 5.0 Vdc, I_D = 50 mAdc)		$V_{DS(on)}$	 – –	 – –	 3.75 0.375	Vdc
Static Drain–Source On–State Resistance (V_{GS} = 10 V, I_D = 500 mAdc) (V_{GS} = 5.0 Vdc, I_D = 50 mAdc) 	 T_C = 25°C T_C = 125°C T_C = 25°C T_C = 125°C	$r_{DS(on)}$	 – – – –	 – – – –	 7.5 13.5 7.5 13.5	Ohms
Forward Transconductance (V_{DS} ≥ 2.0 $V_{DS(on)}$, I_D = 200 mAdc)		g_{FS}	80	–	–	mmhos
DYNAMIC CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	–	–	50	pF
Output Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	–	–	25	pF
Reverse Transfer Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	–	–	5.0	pF
SWITCHING CHARACTERISTICS (Note 2.)						
Turn–On Delay Time	(V_{DD} = 25 Vdc , I_D ≅ 500 mAdc, R_G = 25 Ω, R_L = 50 Ω, V_{gen} = 10 V)	$t_{d(on)}$	–	–	20	ns
Turn–Off Delay Time		$t_{d(off)}$	–	–	40	ns
BODY–DRAIN DIODE RATINGS						
Diode Forward On–Voltage (I_S = 11.5 mAdc, V_{GS} = 0 V)		V_{SD}	–	–	–1.5	Vdc
Source Current Continuous (Body Diode)		I_S	–	–	–115	mAdc
Source Current Pulsed		I_{SM}	–	–	–800	mAdc

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

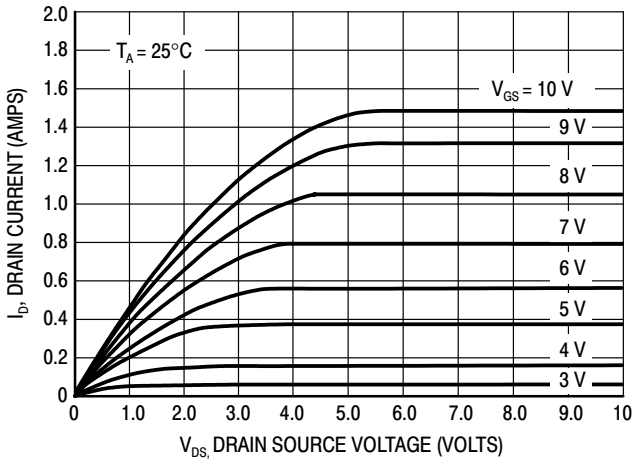


Figure 1. Ohmic Region

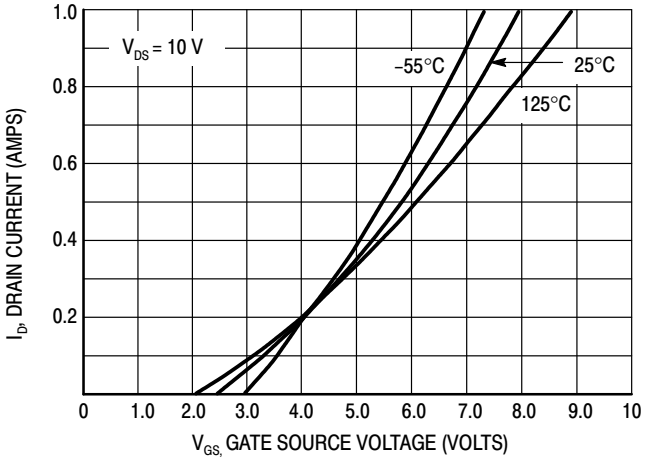


Figure 2. Transfer Characteristics

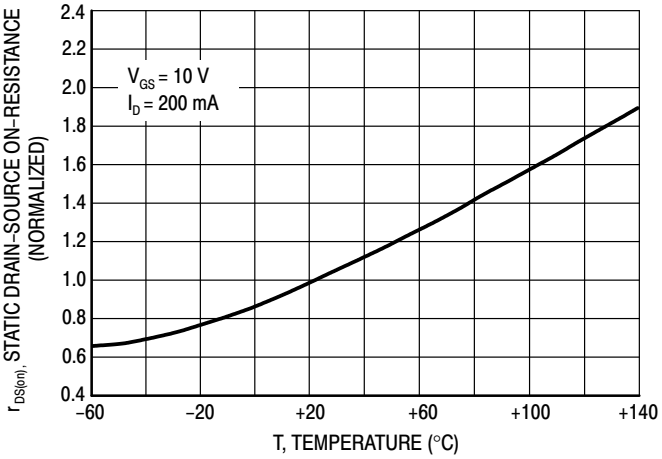


Figure 3. Temperature versus Static Drain–Source On–Resistance

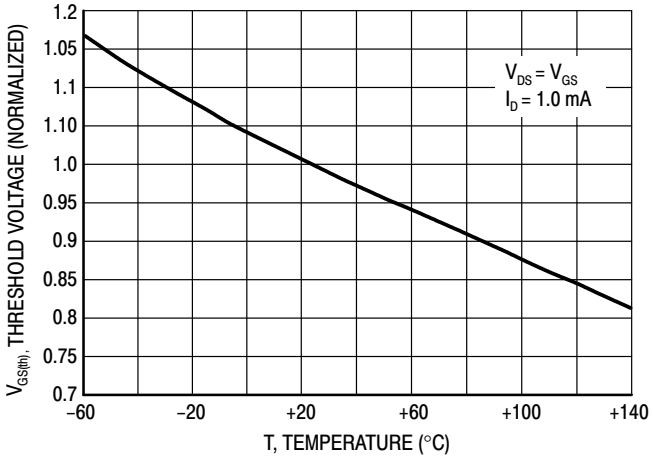


Figure 4. Temperature versus Gate Threshold Voltage